

The author would like to thank H. E. Harvey and J. M. Waring for supplying the crystals.

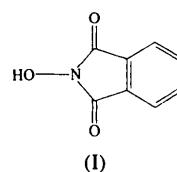
Lists of structure factors, anisotropic displacement parameters, H-atom coordinates for (I) and (II), angles for (I) and bond lengths and angles for (II), have been deposited with the IUCr (Reference: AS1120). Copies may be obtained through The Managing Editor, International Union of Crystallography, 5 Abbey Square, Chester CH1 2HU, England.

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Comment

The title molecule, (I), is planar with a maximum deviation from the molecular plane of 0.03(1) Å and a dihedral angle between the five- and six-membered ring planes of 0.66(7)°. These features are similar to those found in ninhydrin (Medrud, 1969). Our interest is in comparing the geometries of the hydroxamic and amidic groups. Compared with the structure of phthalic anhydride (Bates & Cutler, 1977), the structure of the title compound shows only small differences in bond lengths between chemically equivalent atoms, but the N(1)—C(1)—O(1) [124.6(5)°] and N(1)—C(2)—O(2) [124.9(5)°] bond angles are about 4° larger than the corresponding angles of phthalic anhydride (120.5 and 120.6°, respectively) and are close to the corresponding angles in *N*-phthaloylglycine hydroxamic acid form (I) (123.5 and 124.0°, respectively) and form (II) (123.5 and 124.3°, respectively) (Sikirica & Vickovic, 1980, 1981).



The crystal structure is characterized by intermolecular hydrogen bonds: O(10)…O(1) 2.69(1) Å and O(10)—H(10)…O(1) 167(3)° [symmetry code: (i) $2-x, \frac{1}{2}+y, \frac{1}{2}-z$]. These values are in good agreement with the values for salicylhydroxamic acid (Larsen, 1978), acetohydroxamic acid hemihydrate (Bracher & Small, 1970) and *N*-(3-cyanophenyl)acetohydroxamic acid hydrate (Mochala, Powell & van der Helm, 1984).

The molecular packing is stabilized by hydrogen bonds and van der Waals interactions. In the **b** direction, the molecules are linked into chains by hydrogen bonds.

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N-Hydroxyphthalimide

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Abstract

The title compound, *N*-hydroxy-1*H*-isoindole-1,3(2*H*)-dione, $C_8H_5NO_3$, is virtually planar with a maximum deviation of 0.03(1) Å from planarity. Molecules are connected via hydrogen bonds and van der Waals interactions.

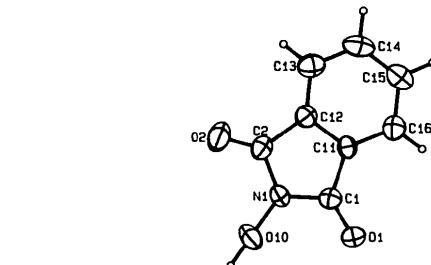


Fig. 1. Molecular structure of the title compound. Displacement ellipsoids are plotted at the 50% probability level.

Experimental

Crystal data

$C_8H_5NO_3$
 $M_r = 163.13$

Mo $K\alpha$ radiation
 $\lambda = 0.71073$ Å

Monoclinic
 $P2_1/c$
 $a = 11.549 (3) \text{ \AA}$
 $b = 3.756 (1) \text{ \AA}$
 $c = 16.442 (8) \text{ \AA}$
 $\beta = 104.94 (3)^\circ$
 $V = 689.1 (4) \text{ \AA}^3$
 $Z = 4$
 $D_x = 1.572 \text{ Mg m}^{-3}$
 $D_m = 1.58 \text{ Mg m}^{-3}$

Data collection

Enraf-Nonius CAD-4
dифрактометр
 $\omega/2\theta$ сканы
Абсорбция коррекция:
эмпирическая
 $T_{\min} = 0.8358$, $T_{\max} = 0.9992$
1309 измеренных отражений
1262 независимых отражений

Refinement

Рефайнмент на F
 $R = 0.041$
 $wR = 0.045$
 $S = 0.685$
535 отражений
125 параметров
Только координаты H атомов
рефинированы

Кристаллолографические параметры из 25 отражений
 $\theta = 5.42\text{--}9.50^\circ$
 $\mu = 0.1151 \text{ mm}^{-1}$
 $T = 298 \text{ K}$
Призма
 $0.5 \times 0.4 \times 0.25 \text{ mm}$
Цвет: бесцветный
Источник кристаллов: из водного раствора

536 измеренных отражений
 $[F_o > 3\sigma(F_o)]$
 $R_{\text{int}} = 0.032$
 $\theta_{\max} = 24^\circ$
 $h = -13 \rightarrow 13$
 $k = 0 \rightarrow 4$
 $l = 0 \rightarrow 18$
3 стандартных отражения
частота: 150 мин
��減: 0.5%

Если $F < 61$ то $w = 1$, иначе
если $F \geq 61$ то $w = (61/F)^2$,
если $F^2 < 3\sigma(F^2)$ то $w = 0$
 $(\Delta/\sigma)_{\max} = 0.01$
 $\Delta\rho_{\max} = 0.169 \text{ e \AA}^{-3}$
 $\Delta\rho_{\min} = -0.189 \text{ e \AA}^{-3}$
Атомные сечение факторы
из *International Tables for X-ray Crystallography*
(1974, том IV)

O(2)—C(2)—N(1) 124.9 (4) C(12)—C(13)—C(14) 117.5 (5)
O(2)—C(2)—C(12) 130.2 (5) C(13)—C(14)—C(15) 122.0 (6)
N(1)—C(2)—C(12) 104.8 (4) C(14)—C(15)—C(16) 120.2 (5)
C(11)—C(16)—C(15) 118.3 (5)

Программа, используемая для анализа: *MolEN* (Fair, 1990).
Программа для решения структуры: *MULTAN11/82* (Main *et al.*, 1982).

Список структурных факторов, анизотропных параметров смещения, координат H-атомов и полной геометрии, включая геометрию H-атомов и углы вращения, опубликован в IUCr (Referenc: AS1104). Копии могут быть получены через Редактора Управления, Международной Ассоциации Кристаллографии, 5 Abbey Square, Chester CH1 2HU, Англия.

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Table 1. Fractional atomic coordinates and equivalent isotropic displacement parameters (\AA^2)

$$B_{\text{eq}} = (4/3)\sum_i \sum_j \beta_{ij} \mathbf{a}_i \cdot \mathbf{a}_j$$

	x	y	z	B_{eq}
O(10)	0.8854 (3)	0.195 (1)	0.2014 (2)	3.83 (8)
O(1)	0.9829 (3)	0.102 (1)	0.3745 (1)	3.49 (8)
O(2)	0.6619 (3)	0.557 (1)	0.1790 (2)	4.66 (9)
N(1)	0.8393 (3)	0.336 (1)	0.2635 (3)	3.02 (9)
C(1)	0.8895 (4)	0.262 (1)	0.3477 (3)	2.7 (1)
C(2)	0.7250 (4)	0.486 (1)	0.2480 (3)	2.8 (1)
C(11)	0.8037 (4)	0.403 (1)	0.3915 (3)	2.5 (1)
C(12)	0.7038 (4)	0.535 (1)	0.3317 (3)	2.7 (1)
C(13)	0.6074 (4)	0.673 (2)	0.3556 (3)	3.5 (1)
C(14)	0.6132 (4)	0.677 (2)	0.4403 (3)	4.1 (1)
C(15)	0.7122 (5)	0.549 (2)	0.5002 (3)	4.0 (1)
C(16)	0.8084 (4)	0.409 (1)	0.4758 (3)	3.4 (1)

Table 2. Selected geometric parameters (\AA , $^\circ$)

O(10)—N(1)	1.374 (5)	C(11)—C(12)	1.399 (6)
O(1)—C(1)	1.213 (5)	C(11)—C(16)	1.372 (7)
O(2)—C(2)	1.209 (5)	C(12)—C(13)	1.374 (7)
N(1)—C(1)	1.384 (6)	C(13)—C(14)	1.377 (8)
N(1)—C(2)	1.397 (8)	C(14)—C(15)	1.388 (8)
C(1)—C(11)	1.467 (6)	C(15)—C(16)	1.379 (8)
C(2)—C(12)	1.470 (7)		
O(10)—N(1)—C(1)	121.5 (4)	C(1)—C(11)—C(12)	108.8 (4)
O(10)—N(1)—C(2)	123.3 (4)	C(1)—C(11)—C(16)	130.2 (5)
C(1)—N(1)—C(2)	113.4 (4)	C(12)—C(11)—C(16)	121.0 (5)
O(1)—C(1)—N(1)	124.6 (5)	C(2)—C(12)—C(11)	108.0 (4)
O(1)—C(1)—C(11)	130.6 (4)	C(2)—C(12)—C(13)	131.0 (5)
N(1)—C(1)—C(11)	104.8 (4)	C(11)—C(12)—C(13)	121.0 (5)

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A Branched Polysilane

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Abstract

2,2,5,5-Tetrakis(trimethylsilyl)-1,1,1,3,3,4,4,6,6,6-decamethylhexasilane, $C_{22}H_{66}Si_{10}$, is a polysilane in which the longest chain is made up of six Si atoms and branching occurs at the second and fifth Si atoms. Each of the two central Si atoms is bonded to a tris(trimethylsilyl)silyl group in an *anti* arrangement. Bond lengths and angles are sufficiently close to normal to indicate that the molecule is relatively unstrained.